## Please refer to Datasheet site below.

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NAND Device ID		NAND Device Parameters								
Manufacturer	Part Number 1	Device Size (bits)	Organization	Class	Block Type	Block Size (bytes)	Page Size (bytes)	Maker Code		Operatin g Voltage
SAMSUNG	K9L8G08U0M	8Gb	1GB	MLC	LB	256K + 8K	2K + 64	ECh	D3h	2.7~3.6V
SAMSUNG	K9HAG08U1M	16Gb	1GBx2	MLC	LB	256K + 8K	2K + 64	ECh	D3h	2.7~3.6V
SAMSUNG	K9G8G08U0M	8Gb	1GB	MLC	LB	256K + 8K	2K + 64	ECh	D3h	2.7~3.6V
SAMSUNG	K9LAG08U0M	16Gb	2GB	MLC	LB	256K + 8K	2K + 64	ECh	D5h	2.7~3.6V
SAMSUNG	K9HBG08U1M	32Gb	2GBx2	MLC	LB	256K + 8K	2K + 64	ECh	D5h	2.7~3.6V
HYNIX	HY27UT084G2M	4Gb	512MB	MLC	LB	256K + 8K	2K + 64	ADh	DCh	2.7~3.6V
HYNIX	HY27UT088G2M	8Gb	1GB	MLC	LB	256K + 8K	2K + 64	ADh	D3h	2.7~3.6V
HYNIX	HY27UU088G5M	8Gb	512MBx2	MLC	LB	256K + 8K	2K + 64	ADh	DCh	2.7~3.6V
HYNIX	HY27UU08AG5M	16Gb	1GBx2	MLC	LB	256K + 8K	2K + 64	ADh	D3h	2.7~3.6V
HYNIX	HY27UW08BGFM	32Gb	1GBx4	MLC	LB	256K + 8K	2K + 64	ADh	D3h	2.7~3.6V
HYNIX	HY27UV08BG5M	32Gb	2GBx2	MLC	LB	256K + 8K	2K + 64	ADh	D5h	2.7~3.6V
ST	NAND04GW3C2A	4Gb	512MB	MLC	LB	256K + 8K	2K + 64	20h	DCh	2.7~3.6V
ST	NAND08GW3C2A	8Gb	1GB	MLC	LB	256K + 8K	2K + 64	20h	D3h	2.7~3.6V